

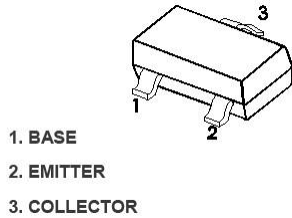
MMBT5401 TRANSISTOR(PNP)

Rev.2.0

SOT-23

SOT-23 贴片塑封三极管

SOT-23 Plastic-Encapsulate Transistors



1. BASE
2. EMITTER
3. COLLECTOR

Marking: 2L

特征 Features

与 MMBT5551 配对; Complementary to MMBT5551
最大功率耗散 300mW; Power Dissipation of 300mW
高稳定性和可靠性。High Stability and High Reliability

机械数据 Mechanical Data

封装: SOT-23 封装 SOT-23 Small Outline Plastic Package
环氧树脂UL 易燃等级Epoxy UL: 94V-0
安装位置: 任意 Mounting Position: Any

极限值和温度特性(TA = 25°C 除非另有规定)

Maximum Ratings & Thermal Characteristics (Ratings at 25°C ambient temperature unless otherwise specified.)

参数 Parameters	符号 Symbol	数值 Value	单位 Unit
Collector-Base Voltage	V _{CBO}	-160	V
Collector-Emitter Voltage	V _{CEO}	-150	V
Emitter -Base Voltage	V _{EBO}	-5	V
Collector Current-Continuous	I _C	-600	mA
Collector Power Dissipation	P _C	300	mW
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55-+150	°C
Thermal resistance From junction to ambient	R _{θJA}	416	°C/W

电特性 (TA = 25°C 除非另有规定)

Electrical Characteristics (Ratings at 25°C ambient temperature unless otherwise specified).

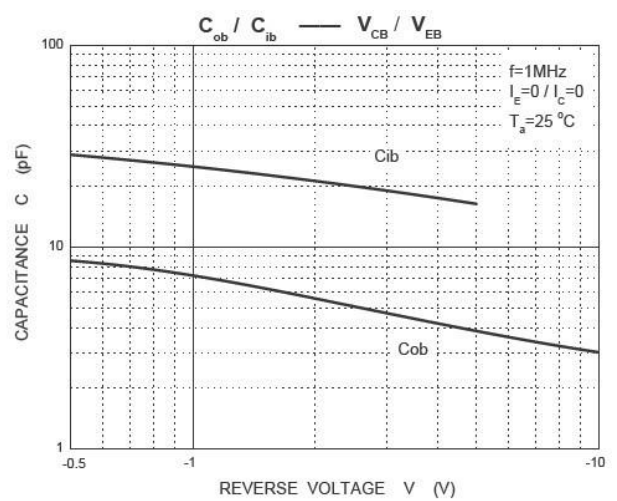
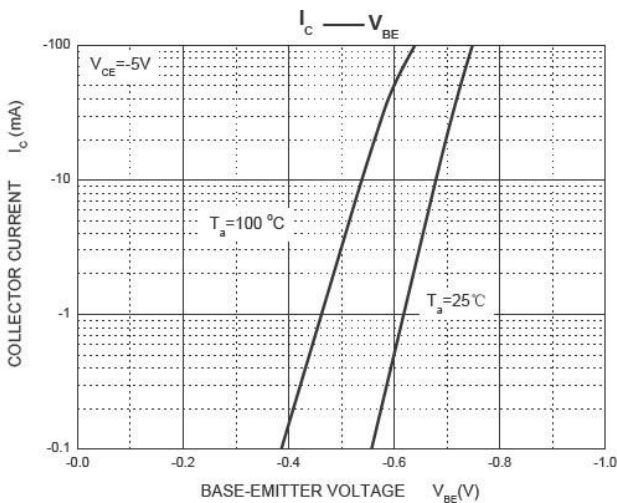
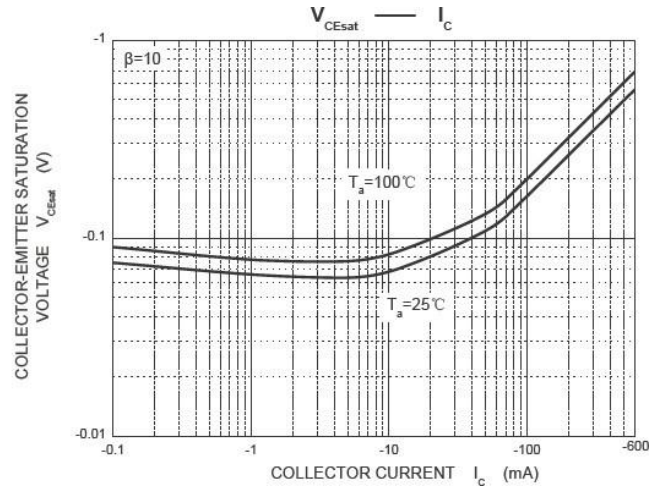
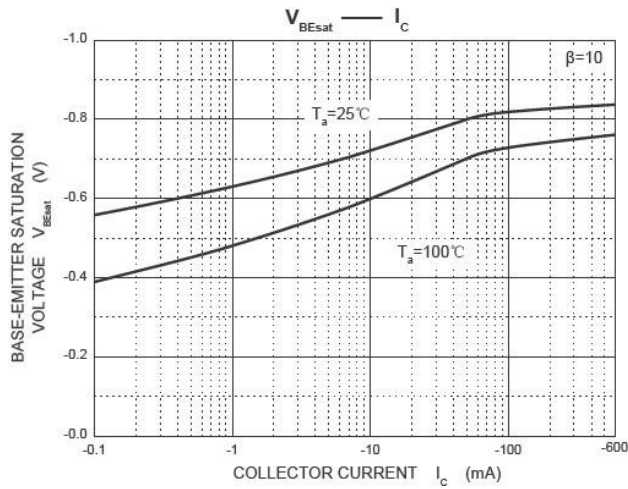
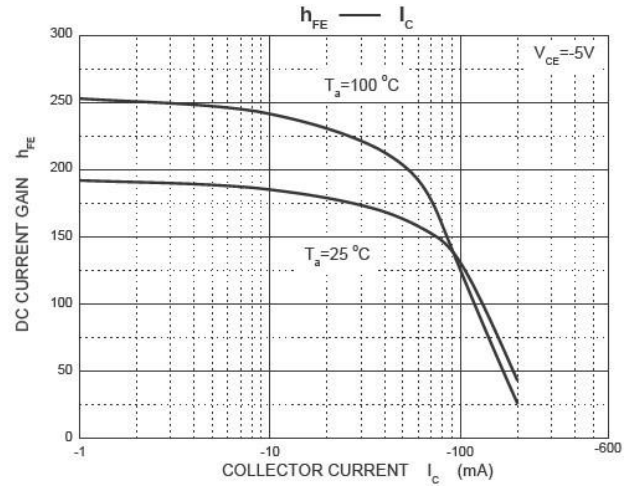
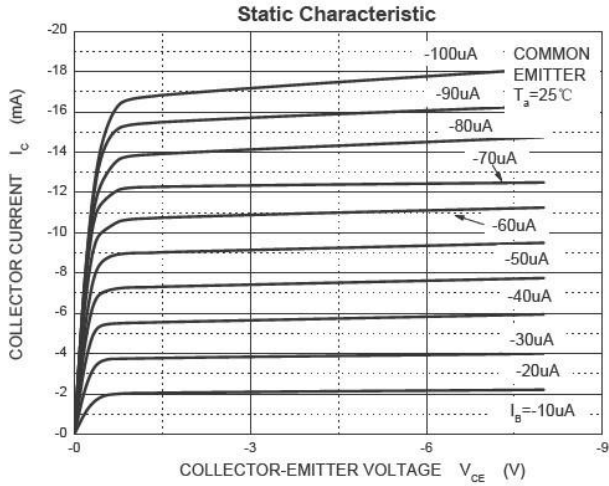
参数 Parameter	符号 Symbols	测试条件 Test Condition	界限 Limits		单位 Unit
			Min	Max	
Collector-base breakdown voltage	V(BR)CBO	I _C =-100uA, I _E =0	-160		V
Collector-emitter breakdown voltage	V(BR)CEO *	I _C =-1mA, I _B =0	-150		V
Emitter-base breakdown voltage	V(BR)EBO	I _E =-10uA, I _C =0	-5		V
Collector cut-off current	I _{CBO}	V _{CB} =-120V, I _E =0		-100	nA
Emitter cut-off current	I _{EBO}	V _{EB} =-4V, I _C =0		-100	nA
DC current gain	h _{FE} (1) *	V _{CE} =-5V, I _C =-1mA	80		
	h _{FE} (2) *	V _{CE} =-5V, I _C =-10mA	100	300	
	h _{FE} (3) *	V _{CE} =-5V, I _C =-50mA	30		
Collector-emitter saturation voltage	V _{CE(sat)1} *	I _C =-10mA, I _B =-1mA		-0.2	V
	V _{CE(sat)2} *	I _C =-50mA, I _B =-5mA		-0.5	V
Base -emitter saturation voltage	V _{BE(sat)1} *	I _C =-10mA, I _B =-1mA		-1.00	V
	V _{BE(sat)2} *	I _C =-50mA, I _B =-5mA		-1.00	V
Transition frequency	f _T	V _{CE} =-5V, I _C =10mA, f=30MHz	100		MHz

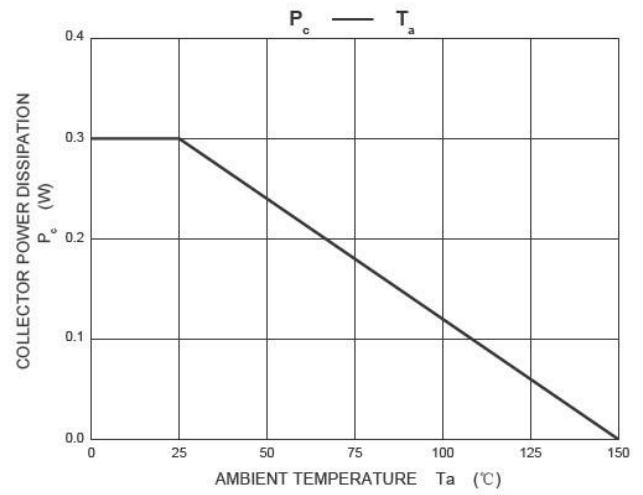
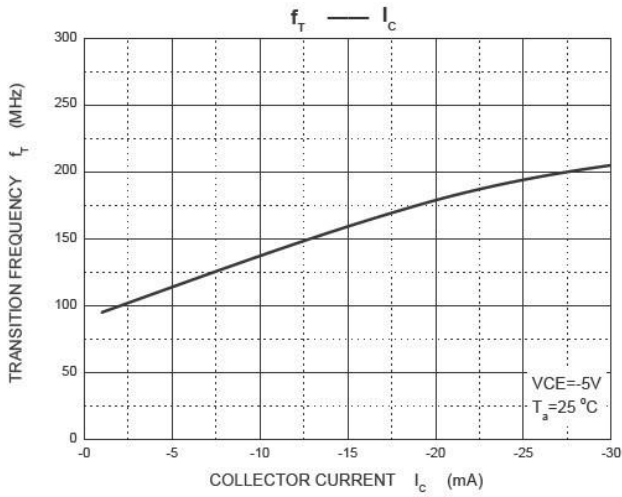
*Pulse test: pulse width ≤ 300us, duty cycle ≤ 2.0%

CLASSIFICATION OF h_{FE}(2)

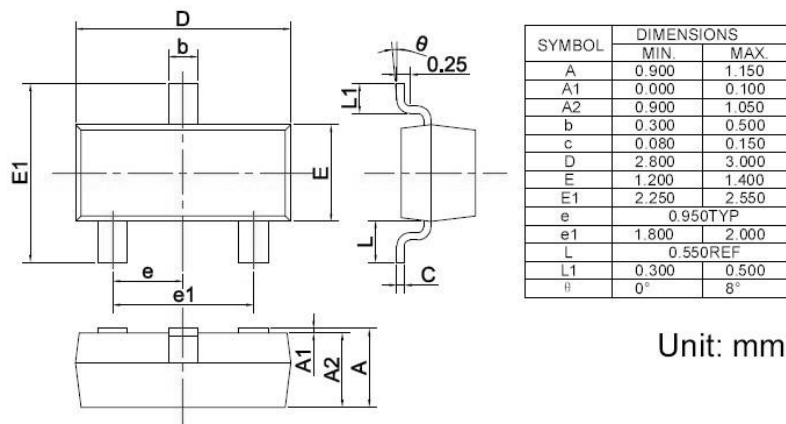
HFE	100-300	
RANK	L	H
RANGE	100-200	200-300

Typical characteristics



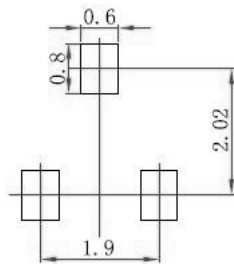


SOT-23 PACKAGE OUTLINE Plastic surface mounted package



焊盘设计参考 Precautions: PCB Design

Recommended land dimensions for SOT-23 diode. Electrode patterns for PCBs



- Note:
1. Controlling dimension: In millimeters.
 2. General tolerance: $\pm 0.05\text{mm}$.
 3. The pad layout is for reference purposes only.

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